1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-3162

2. Structure :

2-1. Planar type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy.

3. Size :

3-1. Chip size : 90.6 mils x 289.4 mils (2.300 mm x 7.350 mm).
3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm).
3-3. Active area : Small: 78.7 mils x 78.7 mils (2.000 mm x 2.000 mm).
Large: 78.7 mils x 196.9 mils (2.000 mm x 5.000 mm).
3-4. Bonding pad (Anode) : 9.8 mils x 9.8 mils (0.250 mm x 0.250 mm)
3-5. Pattern drawing : Refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 ℃)

Parameter	Symbol		Condition	Min.	Typ.	Max.	Unit
※Reverse dark Current	I_D		V_R=10V Ee=0mW/cm^2			10	nA
※Reverse breakdown voltage	$V_{(BR)R}$		I_R=100 μA Ee=0mW/cm^2	60			V
Open circuit Voltage	Voc		T=2856K Ee=5mw/cm^2		390		mV
Short circuit Current	Isc	small	T=2856K Ee=5mW/cm^2		45		μA
		large			115		
Reverse light Current	I_L	small	V_R =5V T=2856K Ee=5mW/cm^2		45		μA
		large			115		
Total Capacitance	C_t	small	V_R =5V Ee=0mW/cm^2 f=1MHz		8		pF
		large			13		

※Based on 100% probing